

IN THE CLAIMS

Please amend the claims as follows.

1. (Original) A method for providing a self heating adjustable titanium disilicon (TiSi_2) resistor, said method comprising the steps of:

placing a triangularly shaped layer of polysilicon on a layer of insulation material;

applying a layer of titanium over said triangularly shaped layer of polysilicon; and

heating said layer of titanium to form a triangularly shaped layer of C49 type titanium disilicon (TiSi_2) in said triangularly shaped layer of polysilicon.

2. (Original) The method as set forth in Claim 1 further comprising the steps of:

coupling a small end of said triangularly shaped layer of polysilicon to an input contact;

coupling a large end of said triangularly shaped layer of polysilicon to an output contact;

coupling an input metal connector to said input contact; and

coupling an output metal connector to said output contact.

3. (Original) The method as set forth in Claim 1 wherein a thickness of said layer of titanium is approximately five hundred Ångstroms (500 Å).

4. (Original) The method as set forth in Claim 1 wherein said step of heating said layer of titanium to form a layer of C49 type titanium disilicon (TiSi_2) in said triangularly shaped layer of polysilicon comprises the step of:

heating said layer of titanium to a temperature of approximately six hundred twenty degrees Centigrade.

5. (Original) The method as set forth in Claim 1 further comprising the step of:
removing unconverted titanium from said layer of C49 type TiSi_2 in said triangularly shaped layer of polysilicon.

6. (Currently Amended) A method for providing a self heating adjustable titanium disilicon (TiSi_2) resistor, said method comprising the steps of: The method as set forth in Claim 1 further comprising the steps of:

placing a triangularly shaped layer of polysilicon on a layer of insulation material;
applying a layer of titanium over said triangularly shaped layer of polysilicon;
heating said layer of titanium to form a triangularly shaped layer of C49 type TiSi_2 in said triangularly shaped layer of polysilicon;

applying a current to said triangularly shaped layer of C49 type TiSi_2 in said triangularly shaped layer of polysilicon; and

converting a portion of said triangularly shaped layer of C49 type TiSi_2 to C54 type TiSi_2 to lower a resistance of said triangularly shaped layer of C49 type TiSi_2 .

7. (Original) The method as set forth in Claim 6 wherein said step of converting a portion of said triangularly shaped layer of C49 type TiSi_2 to C54 type TiSi_2 comprises the steps of:

generating heat from said current in a high resistance portion of said triangularly shaped layer of C49 type TiSi_2 ; and

increasing a temperature of said high resistance portion of said triangularly shaped layer of C49 type TiSi_2 to a temperature that is at least approximately seven hundred degrees Centigrade.

8. (Original) The method as set forth in Claim 7 wherein said conversion of C49 type TiSi_2 to C54 type TiSi_2 in said high resistance portion decreases a resistance of said high resistance portion to a level of resistance where no more C49 type TiSi_2 is converted for said value of current.

9. (Original) The method as set forth in Claim 7 further comprising the step of:
selecting a desired value of resistance for said triangularly shaped layer of C49 type TiSi_2 by
selecting a magnitude of said current.

10. (Original) The method as set forth in Claim 7 further comprising the step of:
decreasing a resistance of said triangularly shaped layer of C49 type TiSi_2 by increasing a
magnitude of said current.

Claims 11-20 (Cancelled).

21. (New) A method, comprising:
forming a triangularly shaped resistor layer comprising C49 type titanium disilicon (TiSi_2);
and
heating the resistor layer to alter a resistance of the resistor layer.
22. (New) The method of Claim 21, further comprising:
coupling a smaller end of the resistor layer to a first contact; and
coupling a larger end of the resistor layer to a second contact.
23. (New) The method of Claim 22, further comprising:
coupling a first metal connector to the first contact; and
coupling a second metal connector to the second contact.
24. (New) The method of Claim 21, wherein forming the resistor layer comprises:
depositing titanium on a triangularly shaped polysilicon layer; and
heating the titanium to form the C49 type TiSi_2 .
25. (New) The method of Claim 24, wherein heating the titanium comprises:
heating the titanium to a temperature of approximately six hundred twenty degrees
Centigrade.

26. (New) The method of Claim 24, wherein the titanium has a thickness of approximately five hundred Ångstroms (500 Å).

27. (New) The method of Claim 21, wherein heating the resistor layer comprises applying a current to the resistor layer to convert a portion of the C49 type TiSi_2 to C54 type TiSi_2 .

28. (New) The method of Claim 27, wherein converting the portion of the C49 type TiSi_2 to C54 type TiSi_2 comprises:

increasing a temperature of a high resistance portion of the C49 type TiSi_2 to a temperature that is at least approximately seven hundred degrees Centigrade.

29. (New) The method of Claim 27, further comprising:
selecting a magnitude of the current to provide a desired resistance for the resistor layer.

30. (New) The method of Claim 27, further comprising:
decreasing the resistance of the resistor layer by increasing a magnitude of the current.